

IN THE SPECIFICATION:

On page 1, after the title and prior to the first full paragraph, which begins at line 2 please insert the following headings and paragraph:

--Cross Reference To Related Applications

This application is a continuation of International Application PCT/EP03/07179 having an international filing date of 4 July 2003 and from which priority is claimed under all applicable sections of Title 35 of the United States Code including, but not limited to, Sections 120, 363 and 365(c).

Technical Field--

On page 1, prior to line 2, please add the following heading:

--Background Art--

On page 1, prior to line 8, please add the following heading:

--Disclosure of the Invention--

On page 3, please amend the paragraph beginning on line 3 as follows:

--That object is attained by a semiconductor capacitor ~~as set forth in claim 1~~according to the invention, an MOSFET ~~as set forth in claim 7~~according to the invention, and a process for the production of a praseodymium silicide layer on a praseodymium oxide layer ~~as set forth in claim 8~~according to

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the invention.—~~The appendant claims recite further advantageous configurations of the semiconductor capacitor.--~~

On page 4, please amend the paragraph beginning at line 21 as follows:

--In accordance with a further aspect of the invention there is provided a process for the production of a praseodymium silicide layer on a praseodymium oxide-bearing layer. According to the invention the praseodymium silicide layer is formed by means of local energy input into regions near the surface of the praseodymium oxide-bearing layer by thermal conversion of praseodymium oxide. Preferably the praseodymium oxide-bearing layer is of praseodymium oxide, at least in its regions which are near the surface. The process according to the fourth aspect of the invention has the advantage that a specific deposition step for the production of the praseodymium silicide layer is eliminated. The process is preferably used in conjunction with the production of a semiconductor capacitor ~~as set forth in claim 1~~according to the invention, or an MOSFET ~~as set forth in claim 7~~according to the invention.--

On page 5, prior to line 12, please add the following heading:

--Brief Description of the Drawings--

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On page 5, prior to line 7, please add the following heading:

--Detailed Description of The Invention--

On page 8, line 1, please eliminate the heading ("CLAIMS") and replace it with the following:

--What is claimed is:--

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